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<u>Diodes Incorporated</u> <u>ZXMN6A11GTA</u>

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Datasheet of ZXMN6A11GTA - MOSFET N-CH 60V 3.1A SOT223

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A Product Line of Diodes Incorporated



ZXMN6A11G

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C	
60V	120mΩ @ V _{GS} = 10V	4.4A	
00 V	180mΩ @ V _{GS} = 4.5V	3.5A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control
- Uninterrupted Power Supply

Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

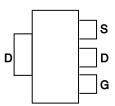
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

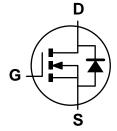




Top View



Pin Out - Top



Equivalent Circuit

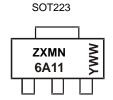
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A11GTA	See below	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



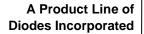
ZXMN6A11 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



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Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units	
Drain-Source Voltage	Drain-Source Voltage			60	V	
Gate-Source Voltage			V_{GS}	±20		
Continuous Drain Current	V _{GS} = 10V	(Note 6) T _A = +70°C (Note 6) (Note 5)	I _D	4.4 3.5 3.1		
Pulsed Drain Current	$V_{GS} = 10V$	(Note 7)	I _{DM}	15.6	A	
Continuous Source Current (Body Diode) (Note 6)		I _S	5			
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	15.6			

Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		2.0 16		
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/°C	
Thermal Decistores, Junction to Ambient	(Note 5)	D.	62.5		
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	32.0	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	R _{θJL}	9.8		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

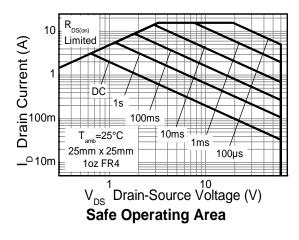
- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as Note 5, except the device is measured at t ≤ 10 seconds.
- 7. Same as Note 5, except the device is pulsed with D = 0.02 and pulse width $300\mu s$.
- 8. Thermal resistance from junction to solder-point (at the end of the drain lead).

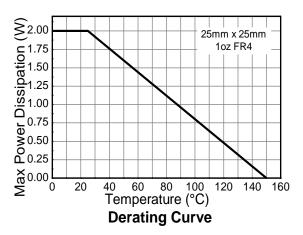


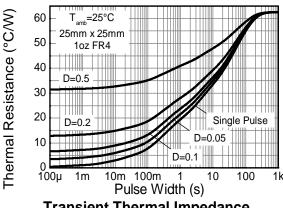


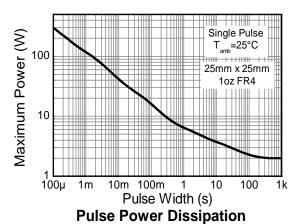
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Thermal Characteristics









Transient Thermal Impedance



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Electrical Characteristics ($@T_A = +25$ °C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS			•		•		
Gate Threshold Voltage	V _{GS(th)}	1.0	_	3.0	V	$I_D = 250 \mu A$, $V_{DS} = V_{GS}$	
Ctatia Dunia Causas On Basistanas (Nata C)		_	0.105	0.120		V _{GS} = 10V, I _D = 2.5A	
Static Drain-Source On-Resistance (Note 6)	R _{DS} (ON)	_	0.150	0.180	Ω	$V_{GS} = 4.5V, I_D = 2A$	
Forward Transconductance (Notes 6 & 7)	g _{fs}	_	4.9	_	S	$V_{DS} = 15V, I_D = 2.5A$	
Diode Forward Voltage (Note 6)	V _{SD}	_	0.85	0.95	V	$I_S = 2.8A$, $V_{GS} = 0V$, $T_J = +25^\circ$	С
Reverse Recovery Time (Note 7)	t _{rr}	_	21.5	_	ns	I _S = 2.8A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 7)	Q _{rr}	_	20.5	_	nC	T _J = +25°C	
DYNAMIC CHARACTERISTICS (Note 7)			•		•	•	
Input Capacitance	C _{iss}		330	_		V _{DS} = 40V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss		35.2	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	17.1	_			
Gate Charge (Note 8)	Qg	_	3.0	_		V _{GS} = 4.5V	
Total Gate Charge (Note 8)	Qq	_	5.7	_	nC	$V_{DS} = 15V$ $V_{GS} = 10V$ $I_{D} = 2.5A$	
Gate-Source Charge (Note 8)	Q _{gs}	_	1.25	_			
Gate-Drain Charge (Note 8)	Q _{qd}		0.86	_			
Turn-On Delay Time (Note 8)	t _{D(on)}		1.95	_			
Turn-On Rise Time (Note 8)	tr		3.5	_		$V_{DD} = 30V, I_D = 2.5A,$ $R_G = 6\Omega, V_{GS} = 10V$	
Turn-Off Delay Time (Note 8)	t _{D(off)}		8.2	_	ns		
Turn-Off Fall Time (Note 8)	t _f		4.6	_			

Notes:

- 6. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.
- 7. For design aid only, not subject to production testing.8. Switching characteristics are independent of operating junction temperature.

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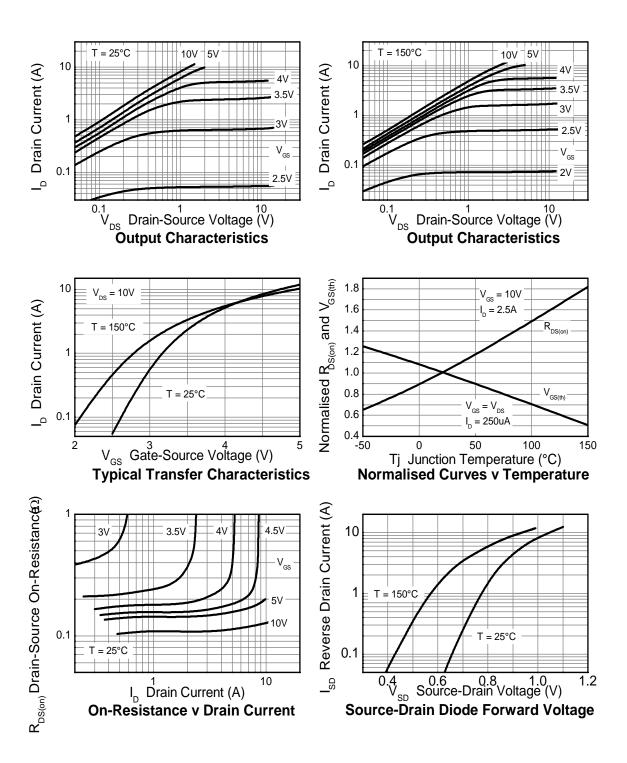
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Typical Characteristics

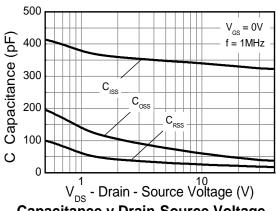


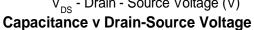


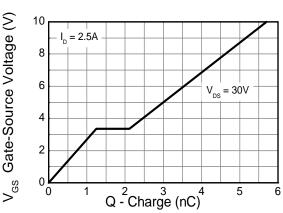


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Typical Characteristics (cont.)

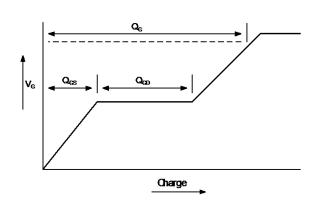




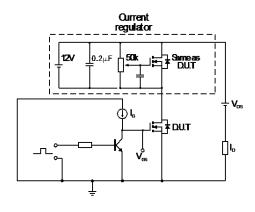


Gate-Source Voltage v Gate Charge

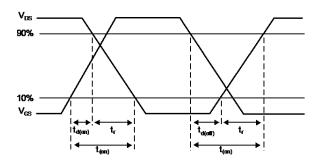
Test Circuit



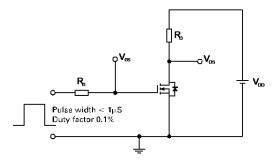
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

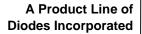


Switching time test circuit

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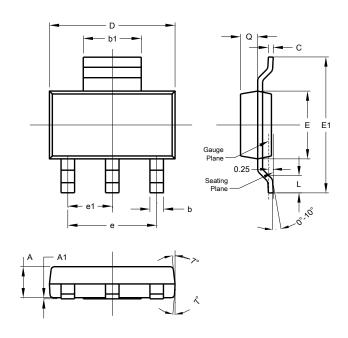




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Package Outline Dimensions

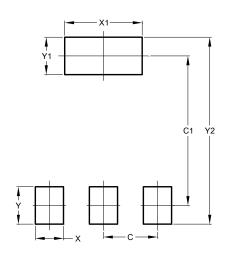
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version



	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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